

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(Currently Amended)** A cleaning solution for surface treatment operations in which metal impurity contamination becomes troublesome comprising an alkaline compound, hydrogen peroxide, water and 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris]~~ and/or 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and nitrilotriacetic acid [NTA; CAS 139-13-9; Titplex-I] as chelating additive(s).
2. **(Currently Amended)** A cleaning solution according to claim 1, wherein ~~characterised in that~~ the alkaline compound is ~~chosen from the group consisting of~~ an organic base, ammonia, ammonium hydroxide, or tetramethyl ammonium hydroxide.
3. **(Currently Amended)** A cleaning solution according to claim 1, wherein ~~characterised in that~~ the alkaline compound is ~~chosen from the group consisting of~~ ammonia and or ammonium hydroxide.
4. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris]~~ in an amount in the range of 1000 to 3000 ppm.
5. **(Currently Amended)** A cleaning solution according to claim 1, comprising nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] in an amount in the range of 100 to 2000 ppm.
6. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris]~~ and nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] in a total amount less than 4000 ppm.
7. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis Tris]~~ and nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] in a total amount less than 2000 ppm.

8. **(Currently Amended)** A method for cleaning a semiconductor substrate ~~substrate(s) comprising the step of treatment of treating~~ the semiconductor ~~substrate substrate(s)~~ with a cleaning solution according to claim 1, and drying said semiconductor ~~substrate substrate(s)~~ after water rinsing.
9. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that the treatment with cleaning solution is carried out at a~~ temperature the range of 20 to 80 °C.
10. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that the treatment with cleaning solution is carried out at normal~~ room temperature.
11. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that said~~ cleaning solution is ~~solutions according to the invention~~ are brought into contact with a surface ~~surfaces~~ to be cleaned for a few seconds to 60 minutes.
12. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that said~~ cleaning solution is ~~solutions according to the invention~~ are brought into contact with a surface ~~surfaces~~ to be cleaned for about 15 seconds to 15 minutes.
13. **(Currently Amended)** A method for treatment of a semiconductor substrate ~~substrate(s)~~ according to claim 8, wherein the semi-conductor substrate ~~substrate(s)~~ is (are) immersed / dipped in the cleaning solution (~~called dipping~~ ~~type cleaning~~).
14. **(Currently Amended)** Use A method for cleaning solutions according to claim 1 for for surface treatment operations including cleaning, etching, polishing, film-forming, for the cleaning of substrates such as semiconductor, metal, glass, ceramics, plastic, magnetic material, superconductors comprising contacting said surface with a cleaning solution according to claim 1.